



CHONGQING CLOUDCHILD TECHNOLOGY CO., LTD

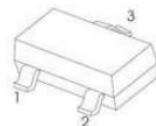
## SOT-23 Plastic-Encapsulate MOSFETs

### BSS138K

N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}TYP$	$I_D$
50 V	0.9Ω@10V	0.34A
	1.0Ω@4.5V	

### SOT-23



### DESCRIPTION

The BSS138K provides excellent  $R_{DS(ON)}$  with low gate charge.

It can be used in a wide variety of applications.

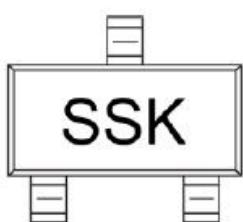
### FEATURE

- High density cell design for extremely low  $R_{DS(on)}$
- Rugged and Reliable
- AEC Q101 Qualified

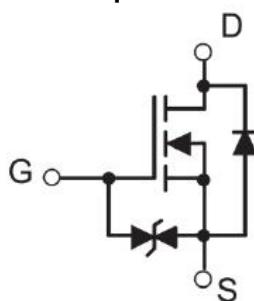
### APPLICATION

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

### MARKING



### Equivalent Circuit



**Maximum ratings ( $T_a=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	50	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	0.34	A
Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~+150	

## MOSFET ELECTRICAL CHARACTERISTICS

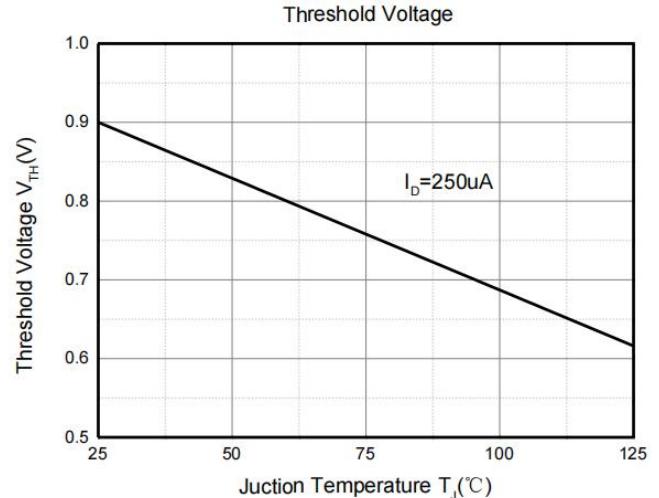
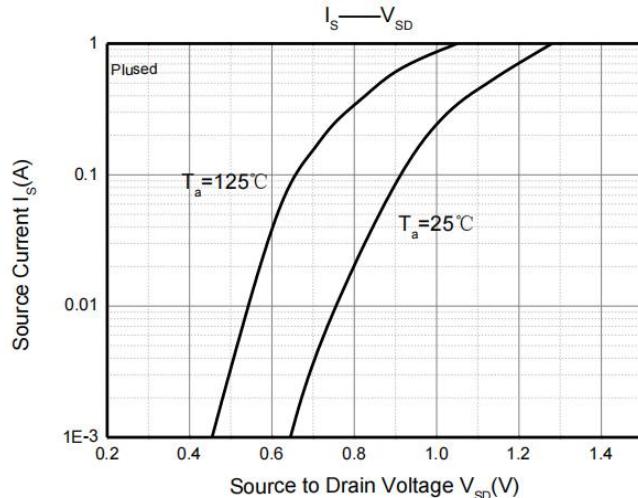
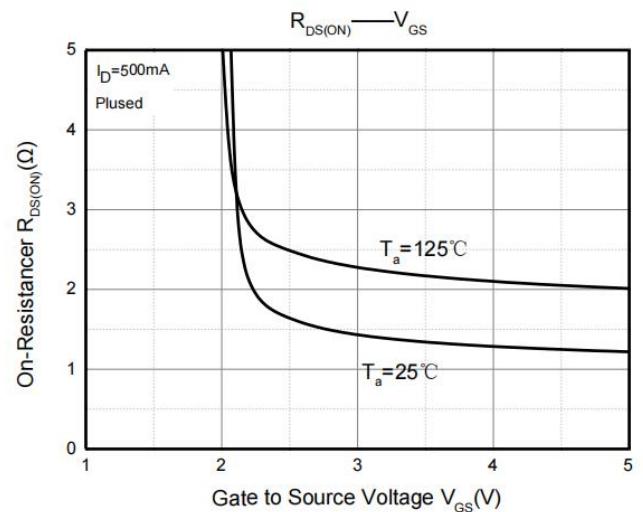
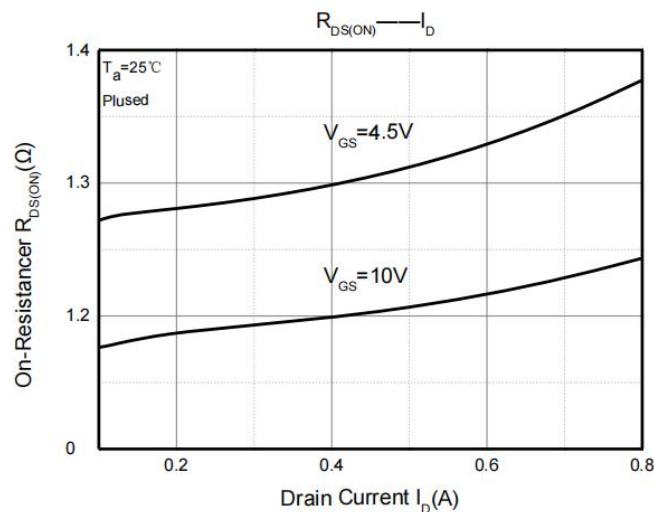
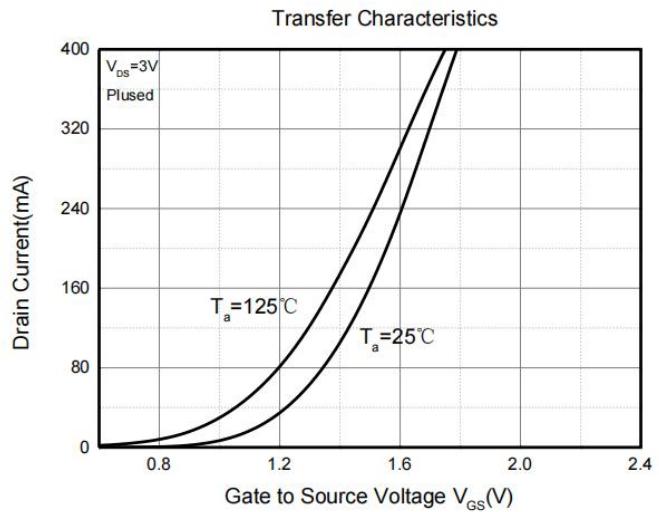
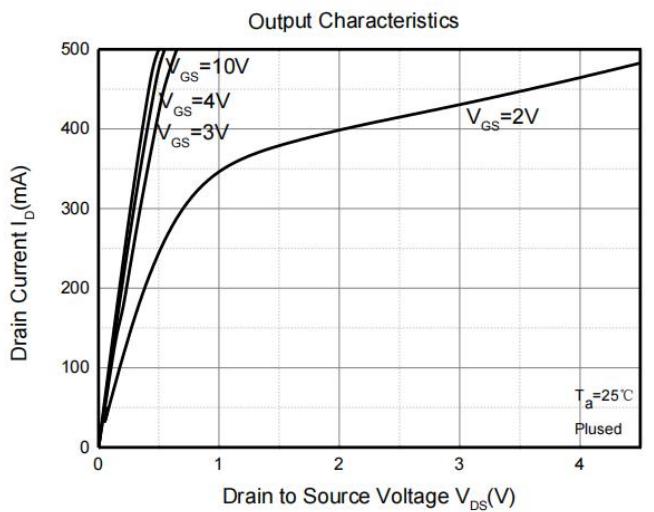
**T<sub>a</sub>=25 °C unless otherwise specified**

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	50			V
Zero gate voltage drain current	I <sub>DSS1</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V			0.5	μA
	I <sub>DSS2</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V			100	nA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±10	μA
Gate threshold voltage <sup>1</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.8	1.1	1.5	V
Drain-source on-resistance <sup>1</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.22A		0.9	2.5	Ω
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.22A		1.0	6.0	
Forward transconductance <sup>1</sup>	g <sub>FS</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.22A		0.13		S
<b>Dynamic characteristics<sup>2</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz		26.5		pF
Output Capacitance	C <sub>oss</sub>			12.9		
Reverse Transfer Capacitance	C <sub>rss</sub>			5.9		
<b>Switching Characteristics<sup>1,2</sup></b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.29A, V <sub>GS</sub> = 10V, R <sub>G</sub> = 6Ω			5	nS
Turn-on rise time	t <sub>r</sub>				18	
Turn-off delay time	t <sub>d(off)</sub>				36	
Turn-off fall time	t <sub>f</sub>				14	
<b>Source-Drain Diode characteristics<sup>1</sup></b>						
Diode Forward voltage	V <sub>SD</sub>	I <sub>s</sub> = 0.44A, V <sub>GS</sub> = 0V		1.15	1.4	V

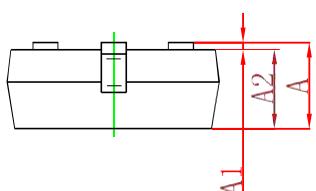
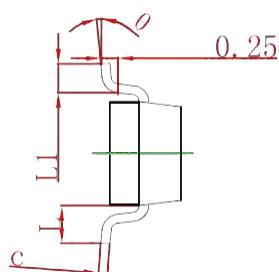
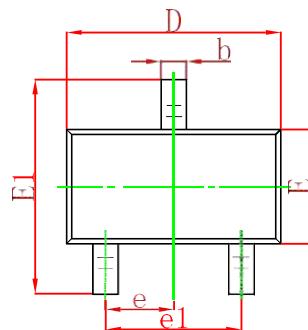
**Notes:**

1. Pulse Test; Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
2. These parameters have no way to verify.

## Typical Characteristics

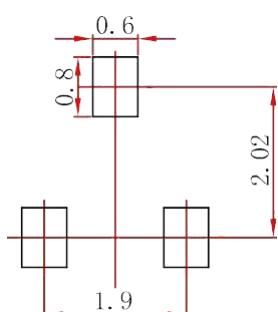


## SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

## SOT-23 Suggested Pad Layout



### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

### NOTICE

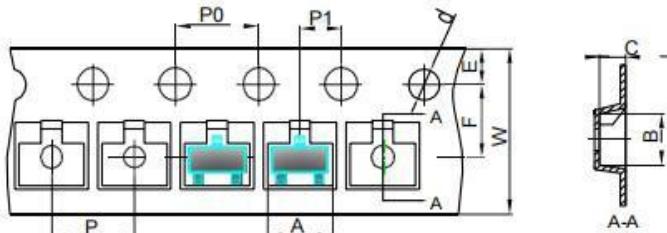
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## SOT-23 Tape and Reel

### SOT-23 Tape and reel

#### SOT-23 Embossed Carrier Tape

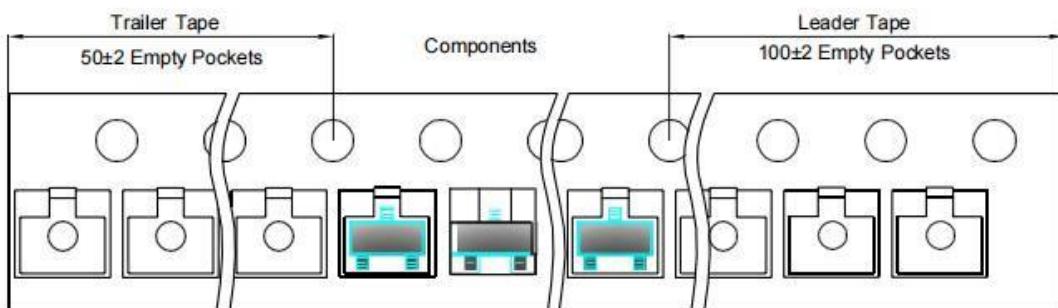


#### Packaging Description:

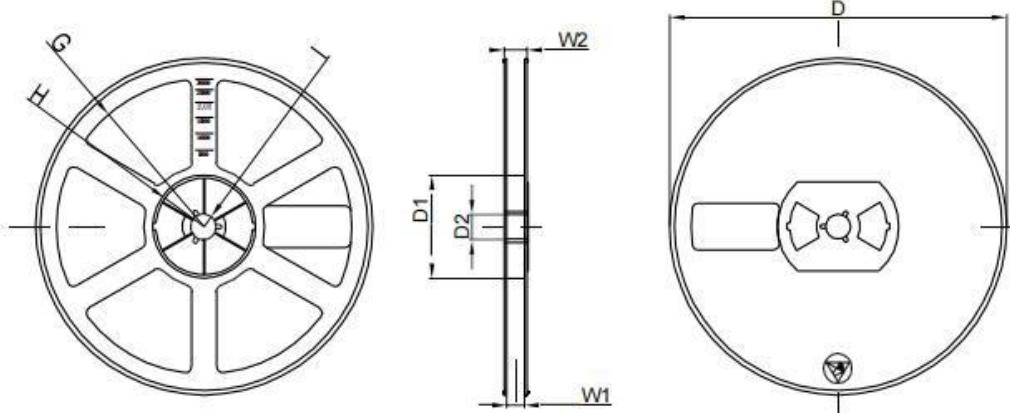
SOT-23 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkgtype	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

#### SOT-23 Tape Leader and Trailer



#### SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

Date of change	Rev #	revise content
2023/07/31	A/0	/